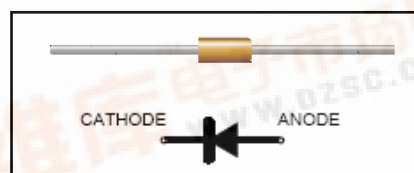


Bi-directional trigger diodes

- . 500mW DO-35
- . Glass silicon
- . We declare that the material of product compliance with RoHS requirements.

DB-4



Product Characteristic

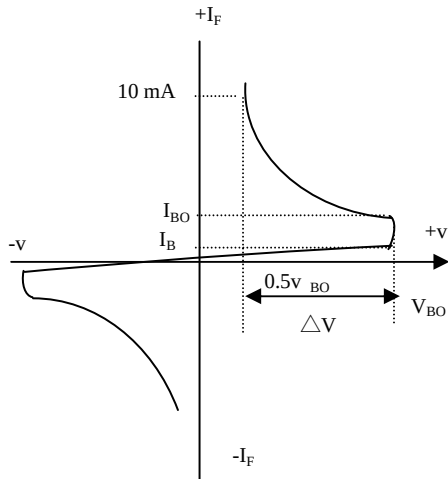
Symbol	Parameter	Test Condition	TYPE	Min	Typ	Max	Unit
V_{BO}	Breakdown Voltage	$I=I_{BO}$	DB-3 DB-4 DB-6	28 35 56	32 40 60	36 45 70	V
$ +V_{BO} - -V_{BO} $	Breakover Voltage Symmetry		DB-3 DB-4 DB-6			3 3 4	V
$ \pm \Delta V $	Dynamic Breakover Voltage	$\Delta I = I_{BO} \text{ to } I_F = 10\text{mA} $	DB-3 DB-4 DB-6	5 5 10			V
V_O	Output Voltage			5			V
I_{BO}	Breakdown Current	$V=V_{BO}$				100	μA
t_r					1.5		μS
I_B	Leakage Current	$V_B=0.5V_{BO} \text{ (max)}$				10	μA

Limiting Values

Symbol	Parameter	Value	Unit
P_c	Power Dissipation	$T_a=50^\circ\text{C}$ 150	mW
I_{Fmax}	Peak Pulse Current	$t_p=10\mu\text{s}$ 120PPS $T_a \leq 40^\circ\text{C}$ DB-3 2.0 DB-4 2.0 DB-6 16	A
T_r T_j	Storage and Operating Junction Temperatuer Range.	-40 to 125 -40 to 110	$^\circ\text{C}$

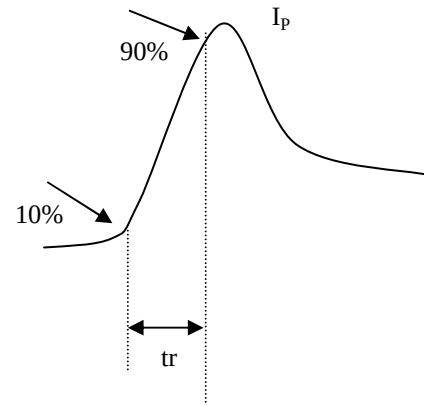
Characteristic Curves

Current-voltage characteristics

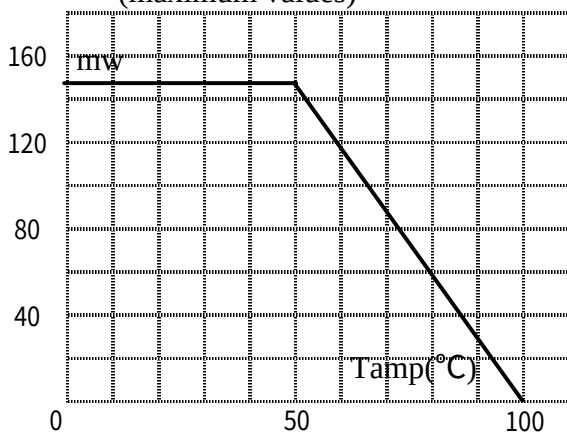


Test circuit see diagram 2

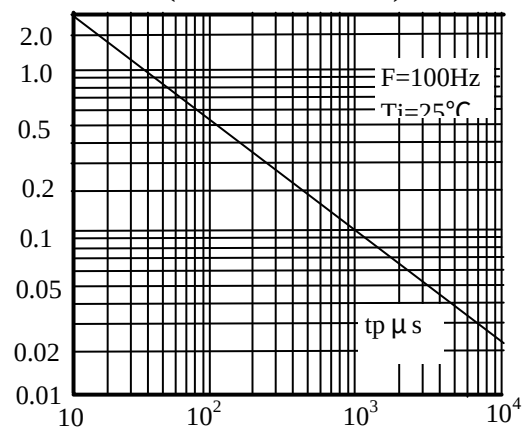
Adjust R for $I=0.5A$



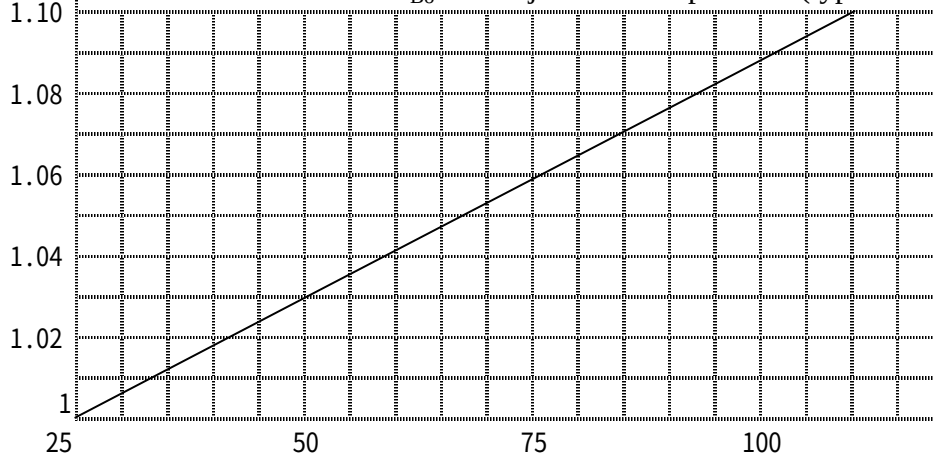
Power dissipation versus ambient temperature
(maximum values)



Peak pulse Current versus pulse duration
(maximum values)



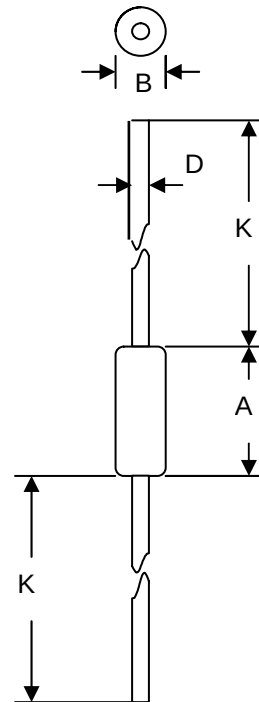
Relative variation of V_{BO} versus junction temperature (typical values)



Package Dimensions in inches and (millimeters)

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	3.6	4.0	0.14	0.157
B	1.6	2.0	0.063	0.079
D	0.4	0.6	0.016	0.024
K	28	30	1.102	1.181

D0-35

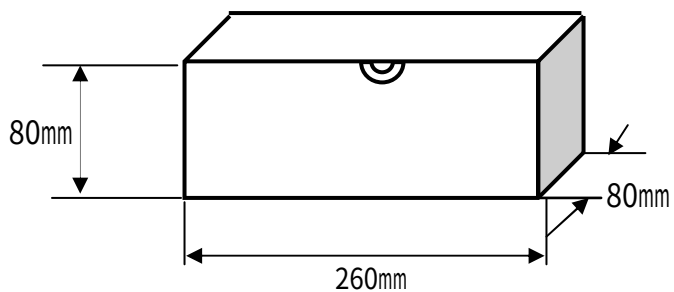


D0-35

Packing

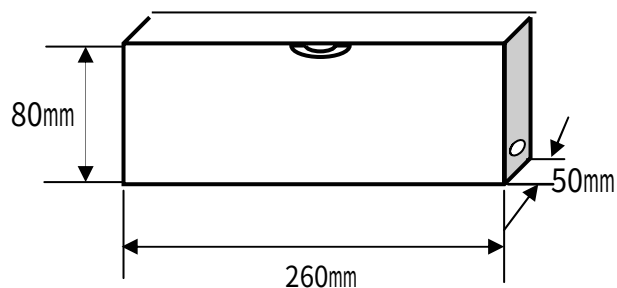
Taping / Box(T52)

Tape Inner Box:5000pcs/each



Taping / Box(T26)

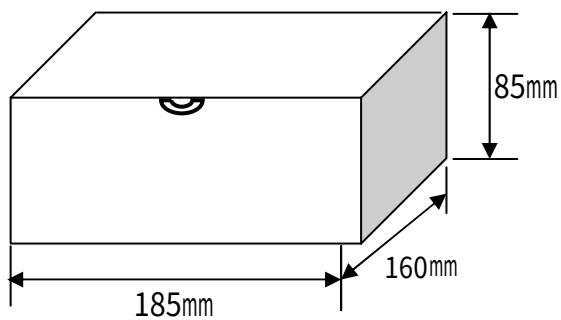
Tape Inner Box:5000pcs/each



Bulk

500pcs/bag

10000pcs /each



Reel (T52)

10000pcs/卷

